

# μ**PD166015GR**

MOS INTEGRATED CIRCUIT

Rev.1.00

Jan 19, 2012

**Data Sheet** 

## Description

The  $\mu$ PD166015 is an N-channel high side driver with built-in charge pump and embedded protection function. It is also a linear solenoid driver with a built-in differential amplifier.

When device is overtemperature or overcurrent is generated in output MOS, the protection function operates to prevent destruction and degradation of the product. When the current flows through the external shunt resistor near the input part of the differential amplifier, the voltage drops at each end of the resistor. The output current can be monitored when the microcomputer reads the output voltage from the amplifier.

### Features

- High temperature operation (Tch =  $175^{\circ}C$  MAX.)
- Built-in charge pump circuit
- Low on-state resistance

 $R_{DS(ON)} = 100 \text{ m}\Omega \text{ MAX.} (V_{IN} = V_{IH}, I_O = 1.5\text{A}, \text{Tch} = 25^{\circ}\text{C})$ 

- Built-in protection circuit
  - Current limitation
  - Overtemperature protection
- Built-in differential amplifier (gain = 8 times)
- Package: Power SOP 8

## Application

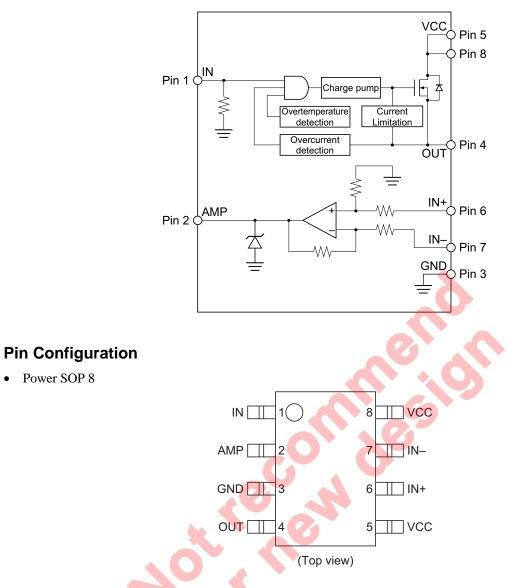
• Switching of all types of 14 V DC grounded loads, such as inductor, resistor and capacitor

## **Ordering Information**

Part No.	Lead Plating	Packing	Package
μPD166015GR-E1-AY	Sn	Tape 2500 p/reel	Power SOP 8
μPD166015GR-E2-AY	Sn	Tape 2500 p/reel	Power SOP 8



## **Block Diagram**



## **Pin Functions**

Pin No.	Pin Name	Function
1	IN	Input pin
2	AMP	Differential amplifier output pin
3	GND	Ground pin
4	OUT	High side output pin
5	VCC	Power supply pin
6	IN+	Differential amplifier + input pin
7	IN–	Differential amplifier – input pin
8	VCC	Power supply pin



## **Absolute Maximum Ratings**

			(Ta = 25)	°C, unless otherwise specified)
ltem	Symbol	Rating	Unit	Condition
Power supply voltage	V <sub>CC1</sub>	-0.3 to +35	V	
	V <sub>CC2</sub>	40	V	τ = 250 ms
IN input voltage	V <sub>IN1</sub>	-0.5 to +7.0	V	IN pin
	V <sub>IN2</sub>	5	V	V <sub>CC</sub> = 0 V, t = 0.5 s, IN pin
IN input current	I <sub>IN</sub>	±10	mA	
Amplifier input voltage	$V_{\text{IN}\pm}$	-1.1 to +18	V	$R_{IN} = 1 \text{ k}\Omega$ , IN+/IN– pin
Amplifier input current	I <sub>IN±</sub>	±10	mA	IN pin, IN+/IN– pin
Output current	I <sub>OA</sub>	2	А	
Output negative voltage	V <sub>OA</sub>	V <sub>CC</sub> -60	V	
Power dissipation	PD	1.50	W	Ta = 25°C <sup>Note</sup>
Operation temperature	Topt	-40 to +125	°C	
Storage temperature	Tstg	-55 to +175	°C	
Current monitor output voltage	V <sub>AMP</sub>	8.0	V	
Current monitor output current	I <sub>AMP</sub>	10	mA	

Note: When mounted on a epoxy PCB (where FR-4 is 10 cm × 10 cm, dimension of copper foil is 15% and thickness of copper foil is 35 μm), PW = 10 s

R07DS0595EJ0100 Rev.1.00



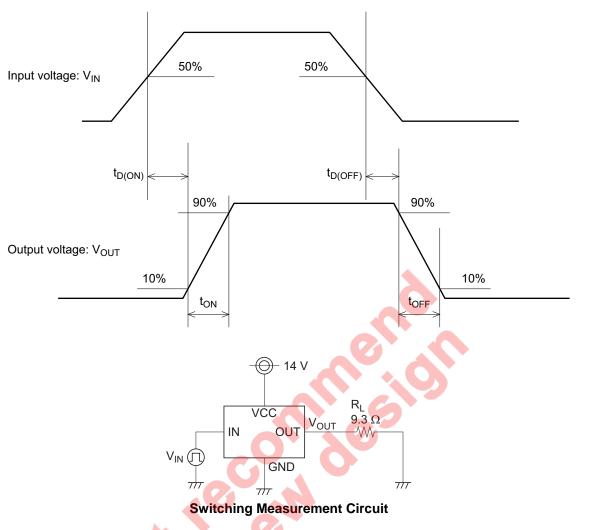
## **Electrical Characteristics**

				$(V_{CC} = 8)$	to 16 V, T	Cch = -40	to +175°C, unless other	wise specified)
ľ	tem	Symbol	MIN.	TYP.	MAX.	Unit	Condition	
Input volta	ge	V <sub>IH</sub>	3.0	_	7.0	V	$V_{CC} = 4.5$ to 16 V	
		V <sub>IL</sub>	0	—	1.0	V		
Input curre	ent	I <sub>IH</sub>	30	—	400	μA	V <sub>IN</sub> = 5.5 V	
		IIL	-10	—	—	μA	$V_{IN} = 0 V$	
Standby cu	urrent	I <sub>CCH</sub>	—	—	7	mA	$V_{IN} = V_{IH} \text{ or } V_{IL}^{Note 1}$	
Output lea	kage current	I <sub>OL</sub>	-0.24	—	—	mA	$V_{IN} = V_{IL}, V_O = 0 V$	
Drain to so	ource on-state	R <sub>DS(ON)</sub>	_	80	100	mΩ	$V_{IN} = V_{IH}, I_O = 1.5 \text{ A}$	Tch = 25°C
resistance				150	180	mΩ		Tch = 150°C
Overcurrer	nt detection	Is	2		(10)	Α	Note 2	•
Overtempe	erature	Tth	(175)	—	—	°C	Note 2	
detection			. ,					
Turn on de	elay time	t <sub>D(ON)</sub>	_	5	50	μs	$R_L = 9.3 \Omega$ , $V_{CC} = 14 V$ ,	
Turn off de	elay time	t <sub>D(OFF)</sub>	_	50	200	μS	V <sub>IN</sub> = 5.0 V–0 V	
Rise time		t <sub>ON</sub>	_	30	200	μs		
Fall time		t <sub>OFF</sub>	_	20	200	μs		
Negative of	output voltage	-Vo	_	_	V <sub>cc</sub> –50	V	$I_0 = -60 \text{ mA}$	
At over	Output	ts	—	—	14	ms	Overcurrent	
current	oscillation					0		
condition	cycle							
	Output on	Ds	—	—	30	%	Overcurrent	
	duty					6		
Amplifier o	utput voltage	VOAMP	0	_	7.5	V	$RL_{AMP} = 50 \ k\Omega$ (connec	t to ground)
range								
Amplifier o	output current	I <sub>OAMP</sub>	—		-0.1	mA	Rsh = 0.25 Ω, lsh = 1.5	0 A,
		(SOURCE)					$V_{OAMP} \times 0.977$	
		IOAMP	0.1	-	—	mA	Rsh = 0.25 Ω, lsh = 1.5	0 A,
		(SINK)					$V_{OAMP} \times 1.023$	
Amplifier slew rate SR <sub>CM</sub>			-	0.3		V/μs	$RL_{AMP} = 50 \ k\Omega$ (connec	t to ground)
Amplifier g	·	GAIN	—	8	—	Times		
Current de	tection	VOGAINW(0.05)	-47.0	—	47.0	%	Rsh = 0.25 Ω	lsh = 0.05 A
accuracy		Vogainw(0.10)	<mark>-2</mark> 3.8		23.8	%	$V_{CC} = 8 \text{ to } 16 \text{ V}$	lsh = 0.10 A
			-16.0	—	16.0	%	$RL_{AMP} = 50 k\Omega$	lsh = 0.15 A
		Vogainw(0.50)	-5.4	_	5.4	%	(connect to ground)	lsh = 0.50 A
		Vogainw(1.00)	-3.1		3.1	%		lsh = 1.00 A
		Vogainw(1.50)	-2.3	—	2.3	%		lsh = 1.50 A
Notoo: 4 OUT ourrout is					•	•	•	•

Notes: 1. OUT current is not included.

2. Not subject to production test, specified by design.

## **Definition of Switching Time**



#### **Truth Table**

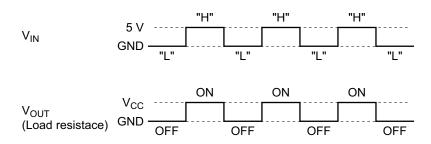
Item	V <sub>IN</sub>	Vout
Normal operation	Н	Н
		L
Overtemperature detection	Н	L
	L	L
Overcurrent detection	Н	Chopping
	L	L



### **Outline of Functions**

#### Pre-Driver (Charge Pump Circuit) ON/OFF Control

When the input voltage of the input pin (IN) is high level (3.0 V or more), the output MOS (Nch) turns on. When the output voltage of the input pin (IN) is low level (1.0 V or less), the output MOS (Nch) turns off. Charge pump circuit is built-in to drive the output MOS (Nch) that is connected to the high side.



#### **Overcurrent Detection Circuit**

This circuit detects overcurrent to output pin (OUT) caused by short circuit etc., and feeds back detection signal to control circuit.

When the overcurrent is detected, the current limitation circuit and the control circuit start operation. The output current is restricted and chopping operation begins.

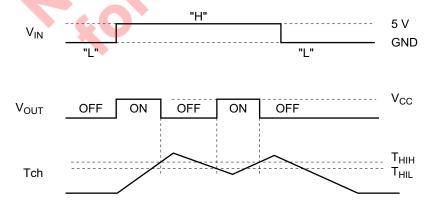
#### **Current Limitation Circuit**

This circuit limits the output current by using the detection signal from the overcurrent detection circuit, preventing destruction and degradation of the product.

#### **Overtemperature Detection Circuit**

This circuit detects overtemperature by output MOS (Nch) driving, and feeds back detection signal to control circuit.

When the circuit detects overtemperature, the protection function of the control circuit operates and output is shutdown. Output MOS (Nch) automatically restarts when channel temperature cools down after shutdown.

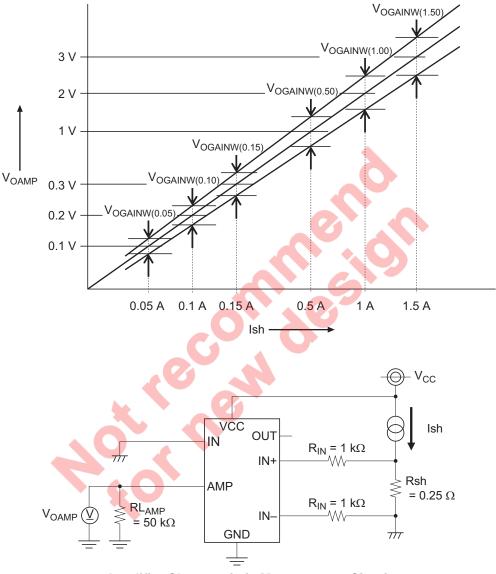




#### **Differential Amplifier Circuit**

This amplifier circuit amplifies the differential input voltage (IN+ and IN–) to the differential amplifier eight times. When the current flows through the external shunt resistor (Rsh) near the input part of the differential amplifier, the voltage drops at each end of the resistor. The output current can be monitored when the A/D converter in the microcomputer reads the output voltage from the amplifier.

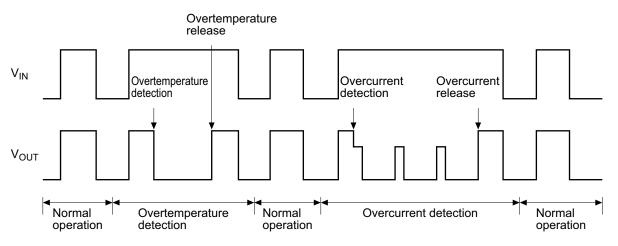
The linear solenoid driver monitors the current through the differential amplifier circuit, and drives constant current by controlling the PWM of the output MOS.



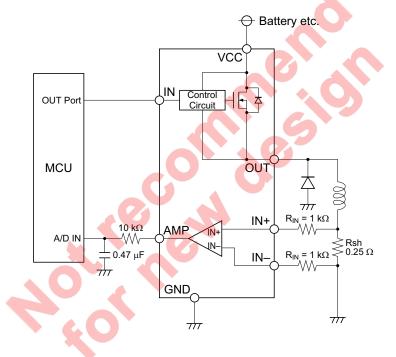
**Amplifier Characteristic Measurement Circuit** 



## **Timing Chart**

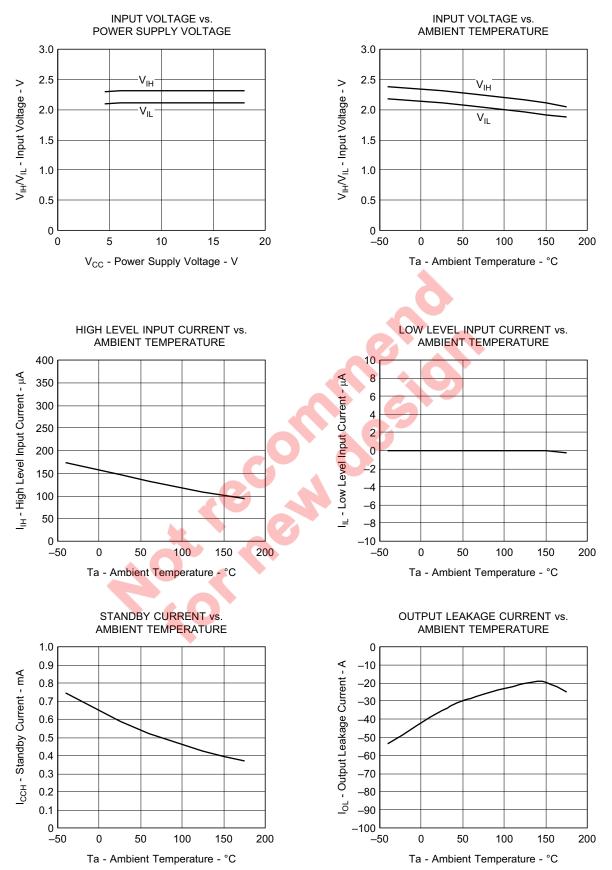


**Example of Application Circuit** 

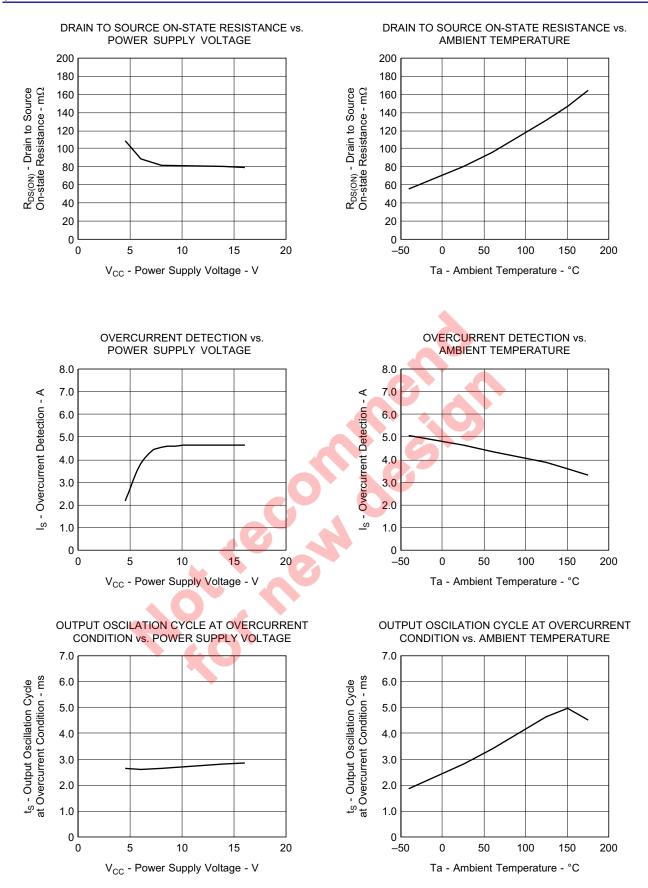


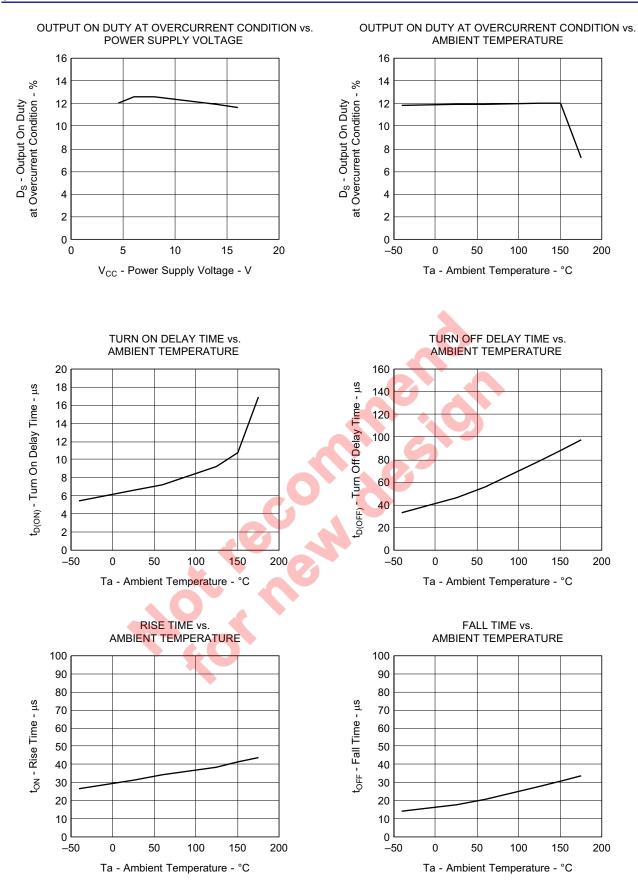


## **Typical Characteristics**

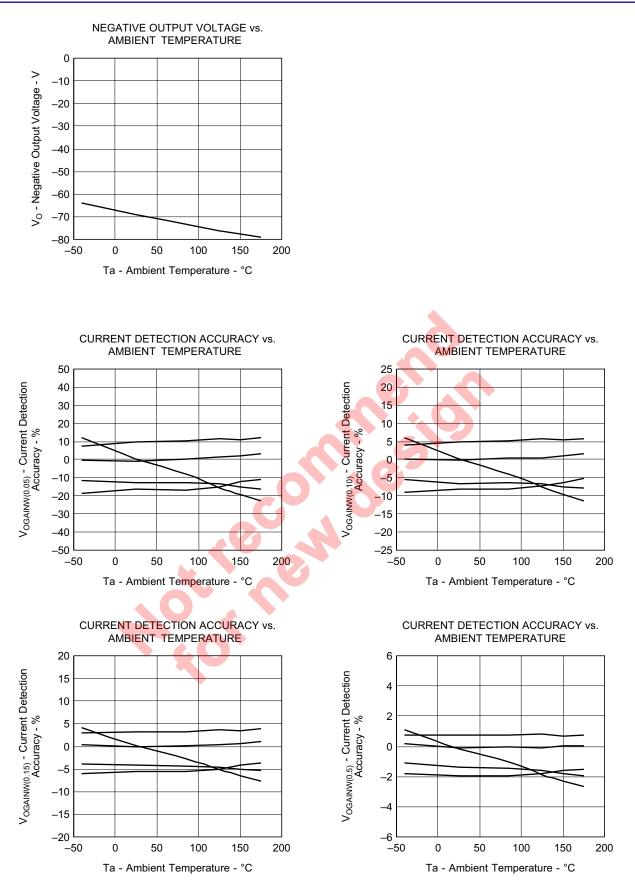


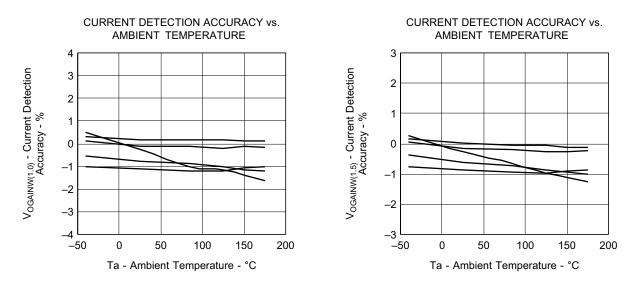




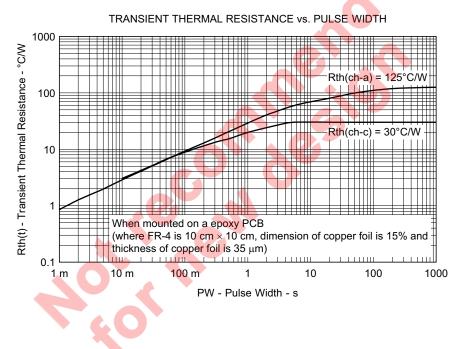






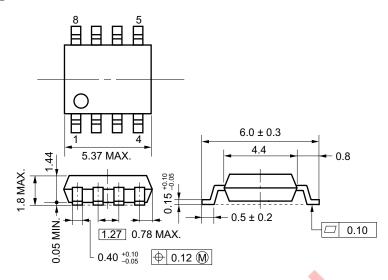


#### **Transient Thermal Resistance Characteristics**



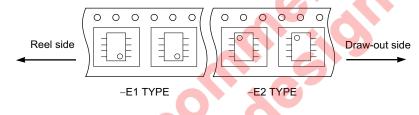


## **Package Drawing**



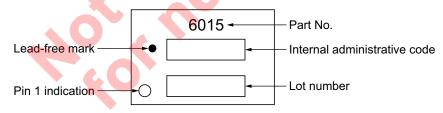
## **Taping Information**

There are two types (-E1, -E2) of taping depending on the direction of the device.



## Marking Information

This figure indicates the marking items and arrangement. However, details of the letterform, the size and the position aren't indicated.





## **Recommended Soldering Conditions**

The  $\mu$ PD166015 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact a Renesas Electronics sales representative.

For technical information, see the following website.

Semiconductor Package Mount Manual (http://www.renesas.com/prod/package/manual/)

- µPD166015GR-E1-AY <sup>Note</sup>: Power SOP 8 •
- µPD166015GR-E2-AY Note: Power SOP 8

Process	Conditions	Symbol
Infrared reflow	Maximum temperature (package's surface temperature): 260°C or below,	IR60-00-3
	Time at maximum temperature: 10 seconds or less,	
	Time at temperature higher than 220°C: 60 seconds or less,	
	Preheating time at 160°C to 180°C: 60 to 120 seconds, Times: Three times,	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	
Partial Heating	Pin temperature: 300°C or below,	_
Method	Heat time: 3 seconds or less (Per each side of the device),	
	Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.	



<b>Revision</b>	History
-----------------	---------

		Description		
Rev.	Date	Page Summary		
1.00	Jan 19, 2012	—	First Edition Issued	



All trademarks and registered trademarks are the property of their respective owners.

#### Notice

- All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
- Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
- 3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
- 4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
- 5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renease Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renease Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
- 6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
- 7. Renesas Electronics products are classified according to the following three quality grades: "Standard", "High Quality", and "Specific". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as "Specific" without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics product for any application for which it is not intended without the prior written consent of Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as "Specific" or the which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is "Standard" unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.
  - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools personal electronic equipment; and industrial robots.
  - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; safety equipment; and medical equipment not specifically designed for life support.
  - "Specific": Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
- 8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
- 9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction provention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
- 10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics.
- 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

Refer to "http://www.renesas.com/" for the latest and detailed information.



SALES OFFICES

#### **Renesas Electronics Corporation**

http://www.renesas.com

Renease Electronics America Inc. 2880 Scott Boulders 1: 4100-8584-6130 Renease Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5041, Fax: +1-005-898-3220 Renease Electronics Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K Tel: +44-1628-585-100, Fax: +44-1628-585-900 Renease Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-21-65030, Fax: +44-1628-585-900 Renease Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China Tel: +49-21-65030, Fax: +49-21-6503-1327 Renease Electronics (Shanghai) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China Tel: +48-10-285-1155, Fax: +486-235-7679 Renease Electronics (Shanghai) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Shanghai 200120, China Tel: +48-10-285-1155, Fax: +486-24-0887-7858 /-7898 Renease Electronics (Shanghai) Co., Ltd. 7th Floor, AzIA Center, No.1233 Luijazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +48-10-285-1156, Fax: +486-24-0887-7858 /-7898 Renease Electronics Hong Kong Limited 7th Floor, 30, Stal K-Center, No.1233 Luijazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +486-24-0587-118, Fax: +4862-2866-9022/9044 Renease Electronics Singapore Pte. Ltd. 13F, No. 363, Fu Shing North Fload, Taipei, Taiwan Tel: +486-24-05175-9607, Fax: +4862-2817-59670 Renease Electronics Malaysia Stn.Bhd. 111905, Bloorking Month Fload, Taipei, Taiwan Tel: +486-24-05407, Fax: +4862-2817-59670 Renease Electronics Malaysia Stn.Bhd. 111907-7955-9390, Fax: +403-7955-9310 Renease Electronics Malaysia Stn.Bhd. 111907, Bloorki, Menara Amcorp, Amcorp Trade Centre, No. 18, Jin Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +65-647-800, Fax: +463-27855-9510 Renease Electronics Malaysia Stn.Bhd. 111905, Bloorki, Menara Amcorp, Amcorp Trade Centre, No. 18, Jin Pe